IN THE CLAIMS

Please amend the claims as follows:

21.   The method of claim 20, wherein forming a performance circuit includes forming a CMOS configuration.

22.   The method of claim 21, wherein coupling the protection circuit to the performance circuit includes coupling the protection circuit to a p-channel device of the CMOS configuration.

23.   The method of claim 21, wherein forming a protection circuit includes forming a diode and coupling the protection circuit to the performance circuit includes coupling the diode to a p-channel device of the CMOS configuration.

24.   The method of claim 20, wherein forming a protection circuit includes forming a unit diode, the unit diode comprised of a block of a doped region of the integrated circuit substrate occupying an area of the substrate sufficient to support a contact to the doped region, a junction region of the integrated circuit substrate surrounding the doped region, and a contact to the doped region.

25.   The method of claim 20, a doped region being a first doped region of a first dopant in a well of the substrate, the well being doped with a first concentration of a second dopant and a junction region separating the first doped region from the well, wherein forming a protection circuit includes forming a third doped region in the well adjacent the junction region, the third doped region doped with a second concentration of the second dopant.

26.   The method of claim 25, wherein forming a protection circuit includes forming a plurality of unit diodes.

27.   The method of claim 20, wherein forming a performance circuit includes:

forming a unit transistor device having a drain region comprised of a doped region of the integrated circuit substrate occupying an area sufficient to support a contact to the doped region;

forming a gate region of the integrated circuit substrate surrounding the doped region; and

forming a contact to the doped region.

29.   The method of claim 28, wherein forming a performance circuit includes:

forming a plurality of unit transistors.